

## **ABSTRACT**

### **WAFER PROCESSING METHOD**

A wafer processing method for dividing a wafer into individual device chips along division lines is disclosed. The wafer processing method includes a modified layer forming step of applying a laser beam having a transmission wavelength to the wafer along each division line in the condition where the focal point of the laser beam is set inside the wafer to thereby form a modified layer inside the wafer along each division line, and a back grinding step of grinding the back side of the wafer as supplying grinding water to reduce the thickness of the wafer to a predetermined thickness and also divide the wafer along each division line where the modified layer is formed as a break start point, thereby obtaining the individual device chips. Prior to performing the back grinding step, the wafer processing method further includes a protective tape attaching step of attaching a protective tape to the front side of the wafer, the protective tape having an adhesive layer curable by the application of ultraviolet light, and an adhesive layer curing step of applying ultraviolet light to the protective tape attached to the front side of the wafer to thereby cure the adhesive layer.

(Figure 3B)